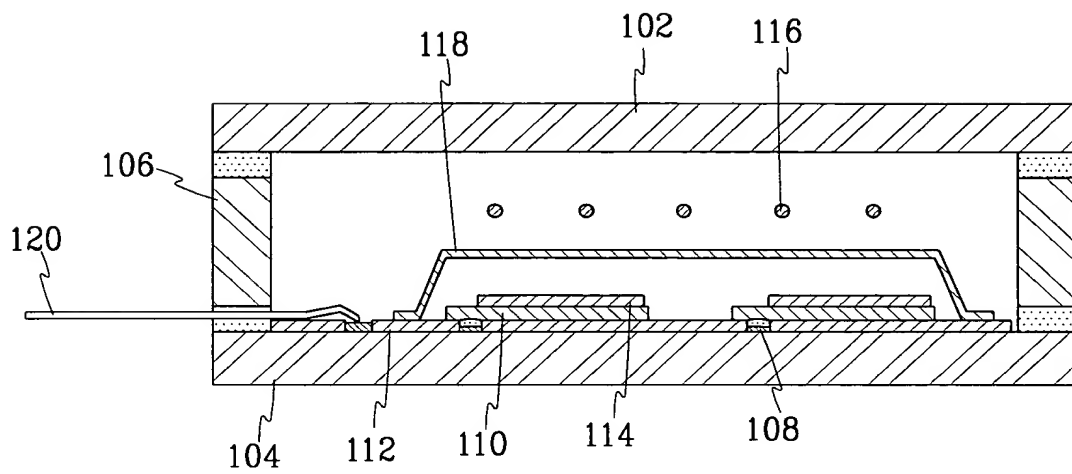


[illegible]

A cross-sectional view of a semiconductor device. A central cavity is formed within a substrate 102. The cavity is bounded by side walls 106 and 118'. The bottom of the cavity is a base layer 104. On the base layer 104, there are several layers of material: a thin layer 108, a thicker layer 110, and a patterned layer 112. A wire 120 is connected to the left side of the device, passing through a hole in the side wall 106. The top surface of the device is a flat layer 116. The bottom surface of the device is a flat layer 114.

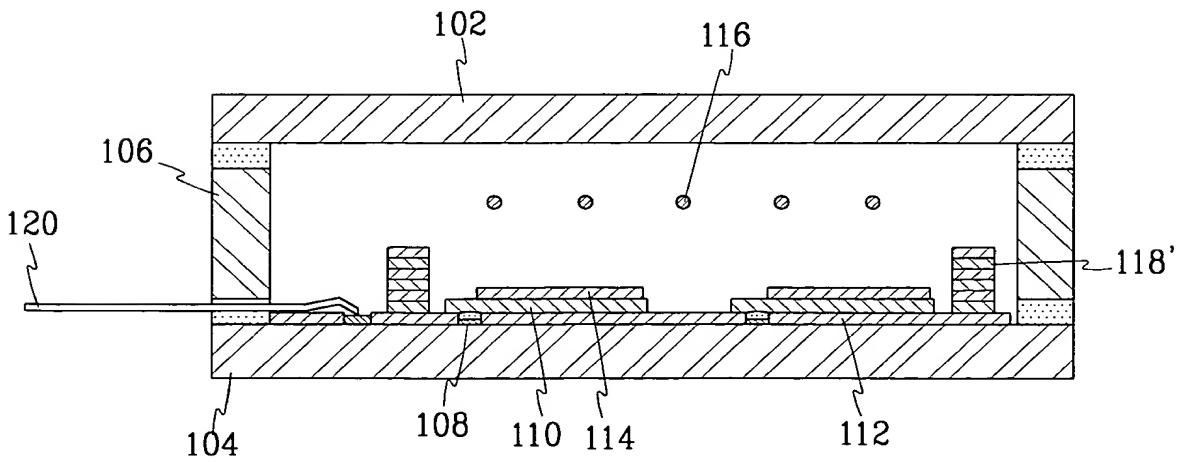


FIG.3

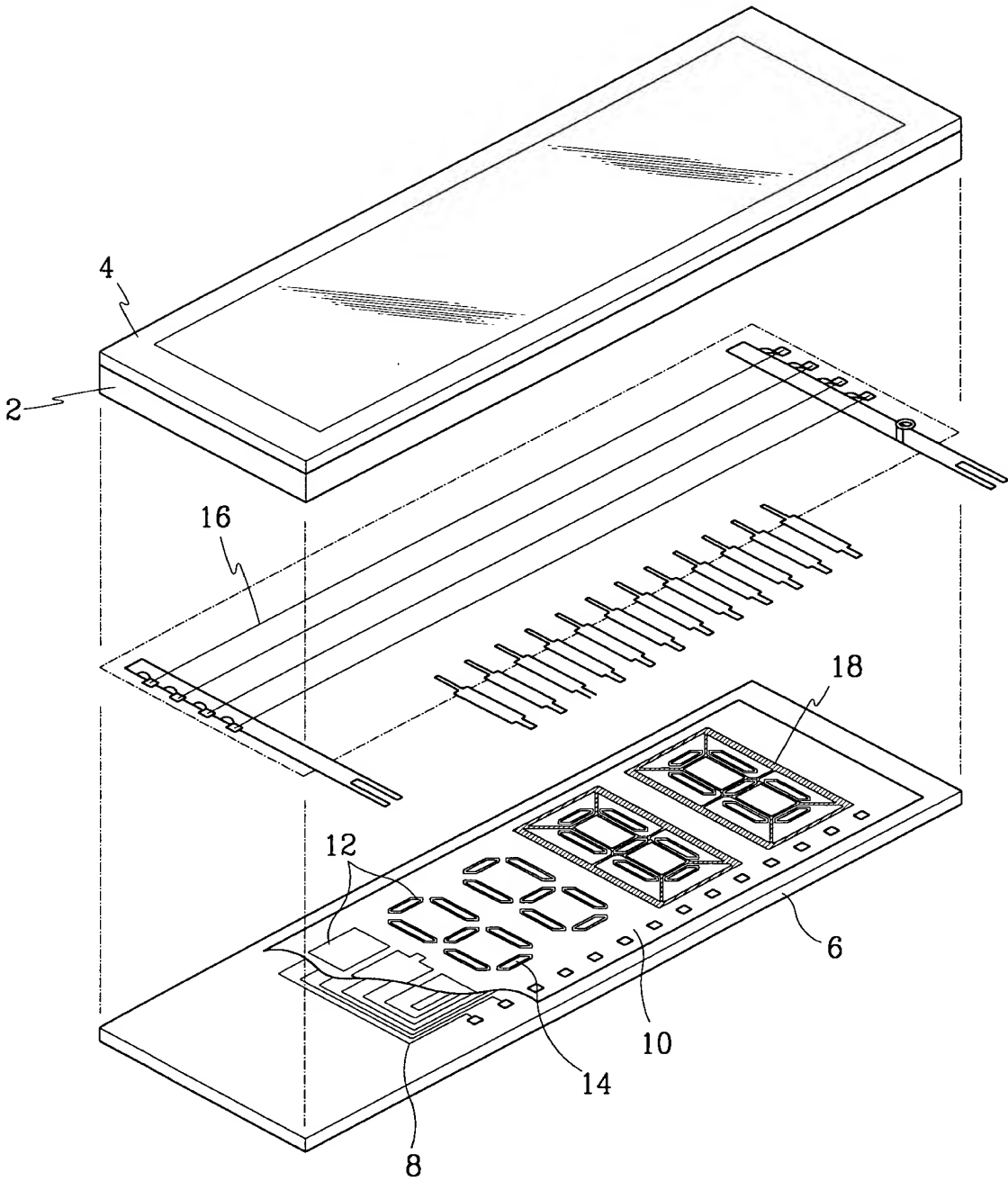


FIG.4

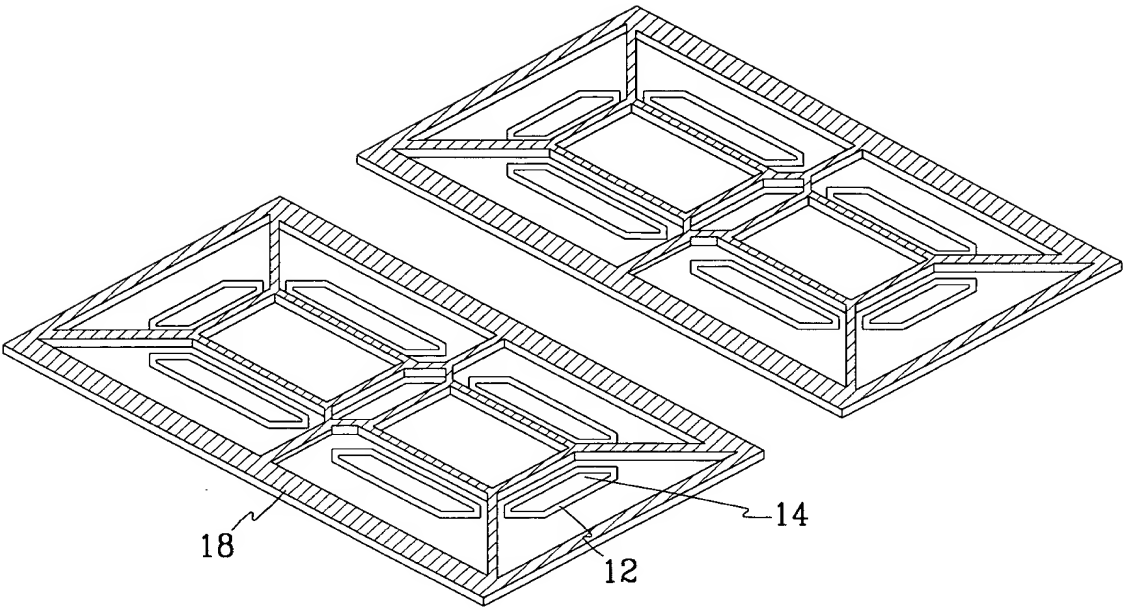


FIG.5

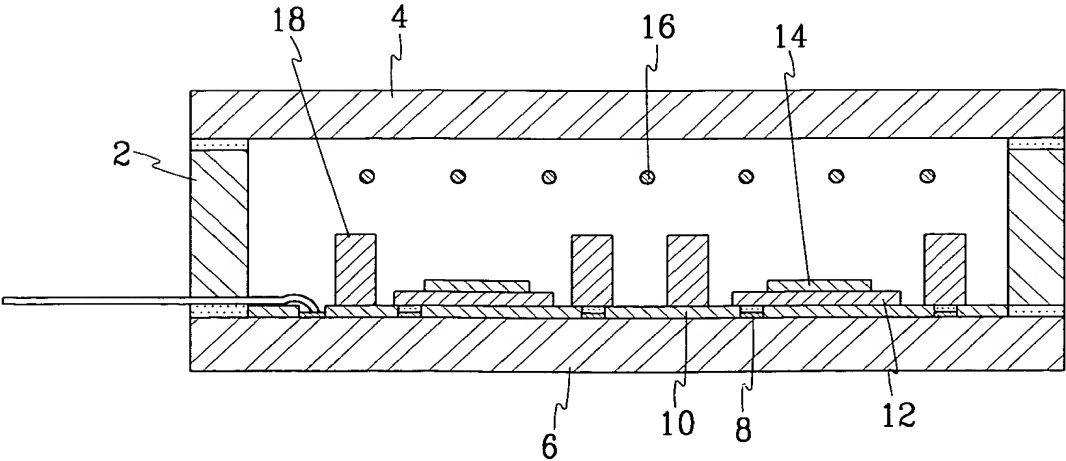


FIG.6

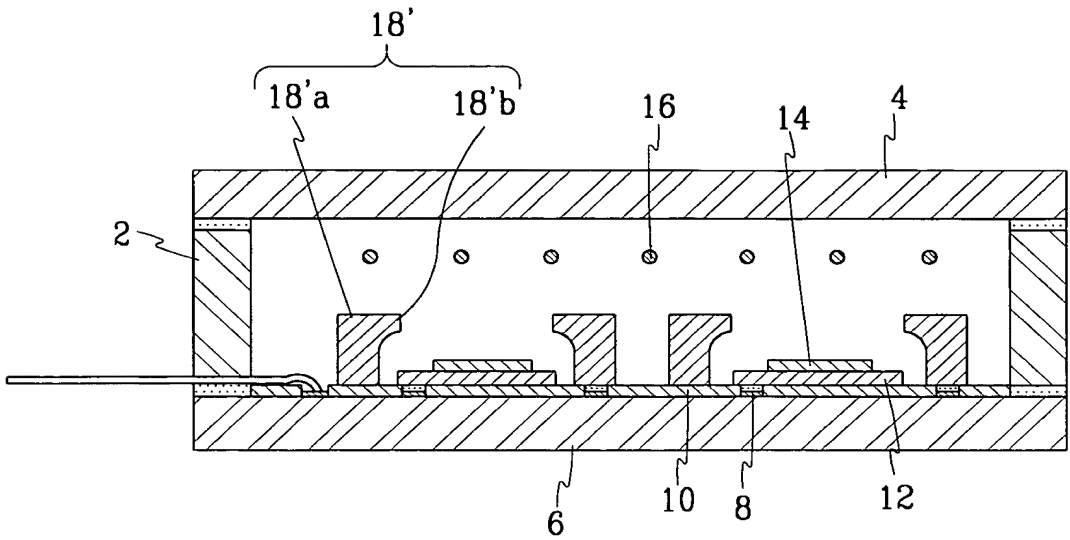


FIG.7

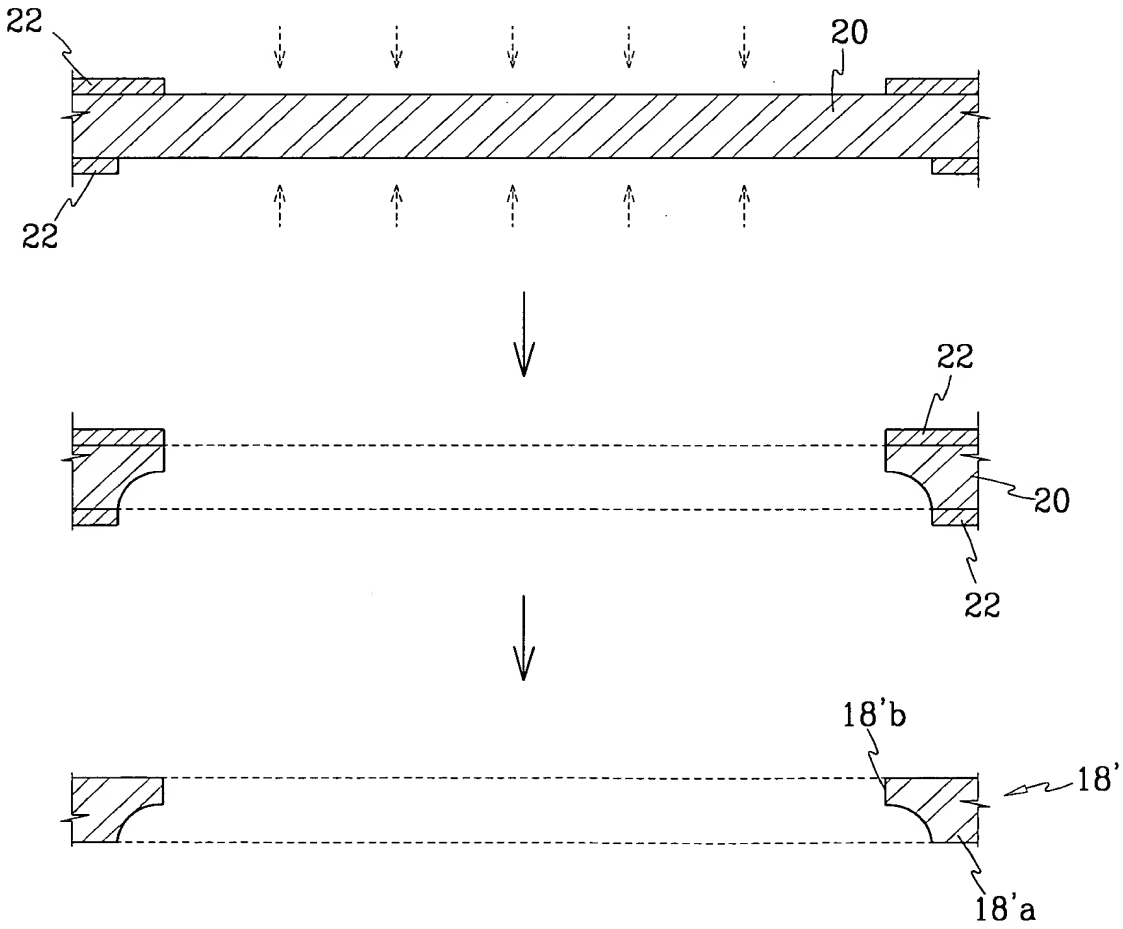


FIG.8

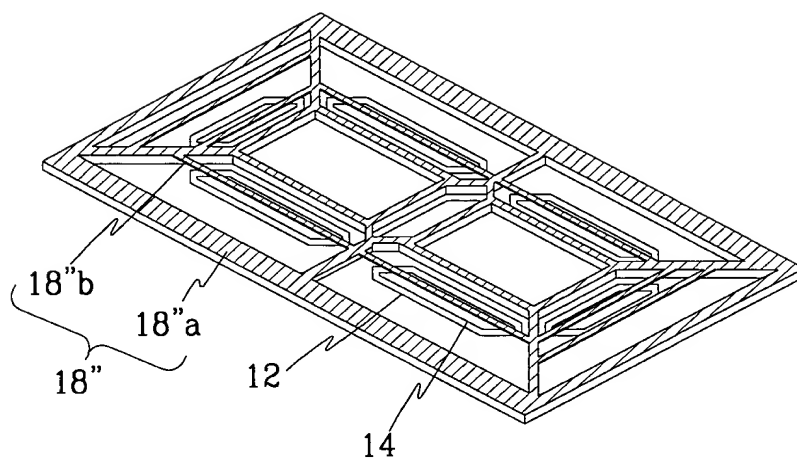


FIG.9

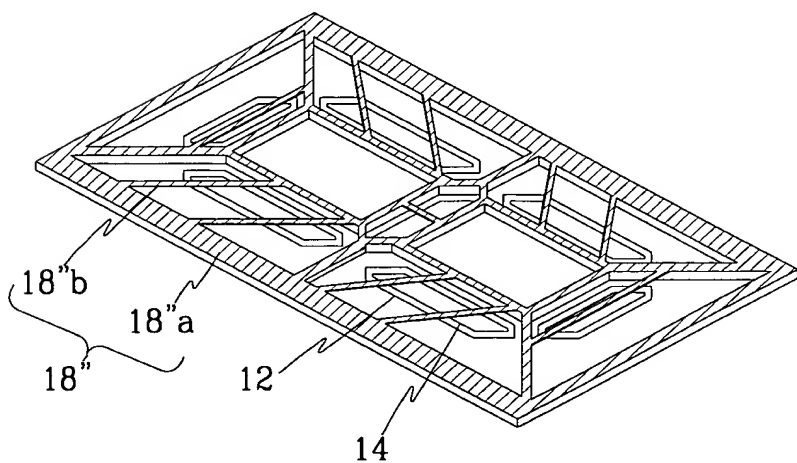


FIG.10

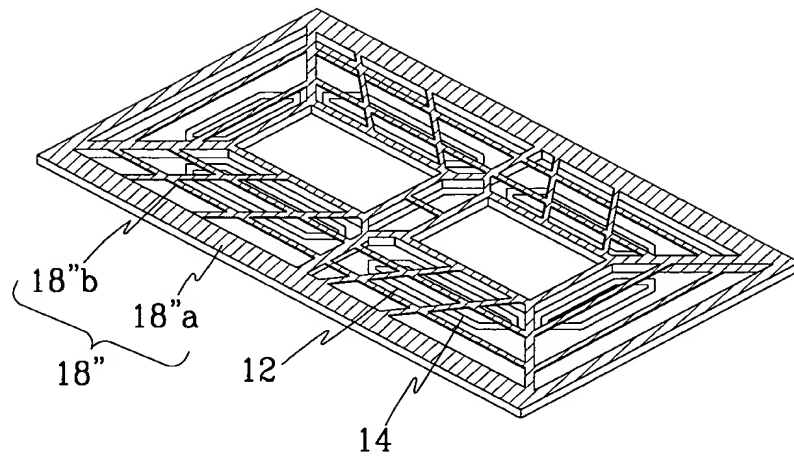


FIG.11

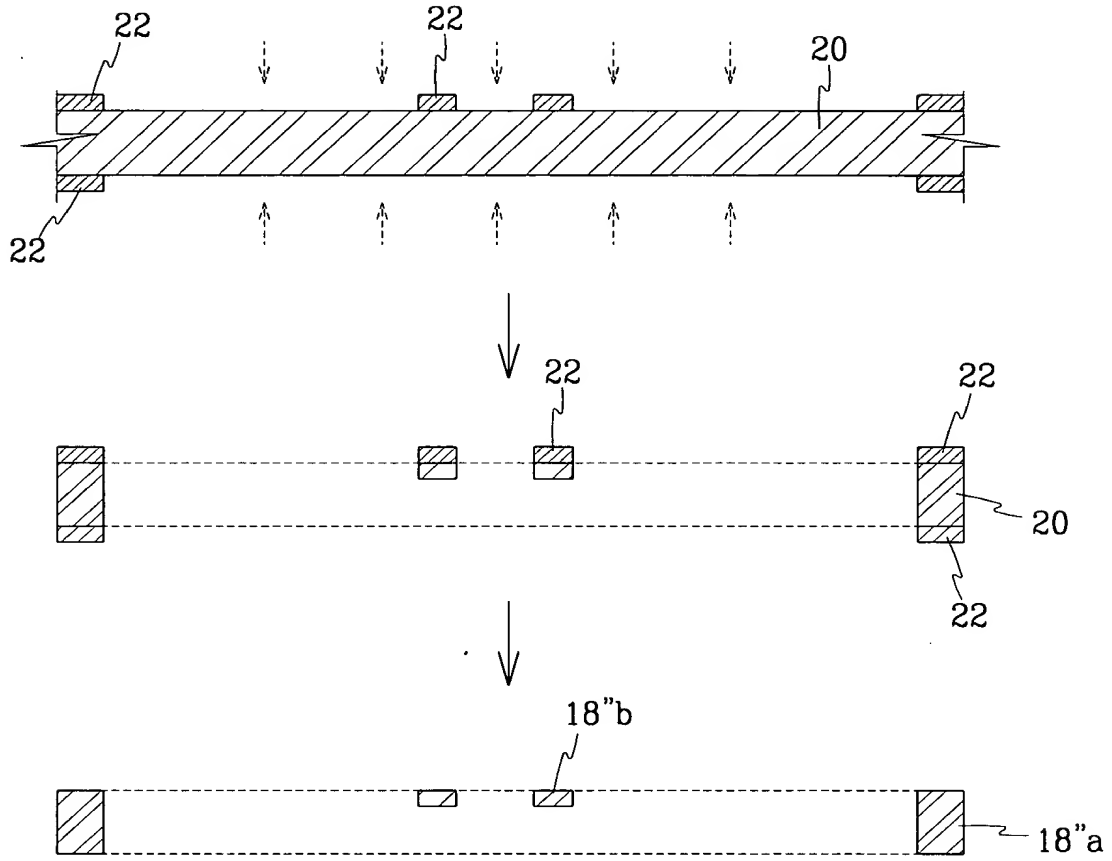


FIG.12

